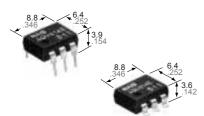
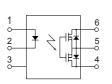
Panasonic

ideas for life

DIP (1 Form B) 6-pin type. Controls load voltage 400V.



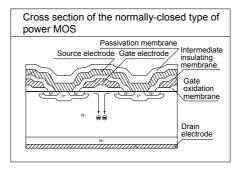
mm inch



FEATURES

1. Low on resistance for normallyclosed type

This has been realized thanks to the built-in MOSFET processed by our proprietary method, DSD (Doublediffused and Selective Doping) method.



GU PhotoMOS (AQV414)

2. Controls low-level analog signals PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

3. High sensitivity, low ON resistance Can control a maximum 0.15 A load current with a 5 mA input current.

4. Low-level off state leakage current The SSR has an off state leakage current of several milliamperes, whereas the PhotoMOS relay has typ. 100 pA even with the rated load voltage of 400 V.

TYPICAL APPLICATIONS

Telepone equipment (Dial pulse)Measuring equipment

TYPES

Туре	I/O isolation voltage	Output rating*			Pa				
				Through hole Surface-mount terminal			Packing quantity		
		age Load Load voltage current	Lood			Tape and reel packing style			
			Tube packing style		Picked from the 1/2/3-pin side	Picked from the 4/5/6-pin side	Tube	Tape and reel	
AC/DC type	1,500 V AC	400 V	120 mA	AQV414	AQV414A	AQV414AX	AQV414AZ	1 tube contains 50 pcs. 1 batch contains 500 pcs.	1,000 pcs.

*Indicate the peak AC and DC values.

Note: For space reasons, the SMD terminal shape indicator "A" and the package type indicator "X" and "Z" are omitted from the seal.

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

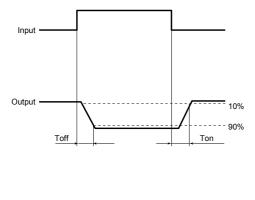
	0 (,		
	Symbol	Type of connec- tion	AQV414(A)	Remarks		
Input	LED forward current	lF	\backslash	50 mA		
	LED reverse voltage	VR		5 V		
	Peak forwrd current	IFP Pin		1 A	f = 100 Hz, Duty factor = 0.1%	
	Power dissipation			75 mW		
Output	Load voltage (peak AC)	VL		400 V		
		IL.	A	0.12 A	A connection: Peak AC, DC B,C connection: DC	
	Continuous load current		В	0.13 A		
			С	0.15 A		
	Peak load current	Ipeak		0.3 A	A connection: 100 ms (1 shot), V _L = DC	
	Power dissipation	Pout		500 mW		
Total power dis	Ρτ		550 mW			
I/O isolation vo	Viso		1,500 V AC			
Temperature limits	Operating	Topr		-40°C to +85°C -40°F to +185°F	Non-condensing at low temperatures	
	Storage	Tstg		-40°C to +100°C -40°F to +212°F		

GU PhotoMOS (AQV414)

		*	-		Type of			
	m		Symbol	connec- tion	AQV414(A)	Condition		
	LED operate (OFF) current		Typical	IFoff		1.0 mA	I∟= 120 mA	
			Maximum			3.0 mA	1L= 120 mA	
loout	I ED reverse (ON) current		Minimum	1-	_	0.4 mA	I∟= 120 mA	
Input			Typical	Fon		0.95 mA		
	LIED dropout voltade –		Typical	VF	_	1.25 V (1.14 V at I⊧= 5 mA)	I⊧= 50 mA	
			Maximum			1.5 V		
	On resistance		Typical		A	26 Ω	I⊧ = 0 mA	
			Maximum	Ron		50 Ω	I∟= Max. Within 1 s on time	
			Typical	Ron	В	20 Ω	I⊧= 0 mA I∟= Max. Within 1 s on time	
Output			Maximum			25 Ω		
•		Typical		С	10 Ω	I⊧= 0 mA I∟= Max. Within 1 s on time		
		Maximum	Ron		12.5 Ω			
	Off state leakage current		Maximum	Leak	_	1 μΑ	l⊧= 5 mA V∟ = 400 V	
Transfer characteristics	Switching speed	Operate (OFF) time*	Typical	Toff	_	0.47 ms	$I_F = 0 \text{ mA} \rightarrow 5 \text{ mA}$	
			Maximum			1.0 ms	l∟ = 120 mA	
		Reverse	Typical Maximum	Ton	_	0.28 ms	I⊧= 5 mA → 0 mA I∟ = 120 mA	
		(ON) time*				1.0 ms		
	I/O capacitance		Typical	Ciso		0.8 pF	f = 1 MHz V _B = 0 V	
			Maximum			1.5 pF		
	Initial I/O isolation resistance		Minimum	Riso	_	1,000 MΩ	500 V DC	

Note: Recommendable LED forward current IF= 5 mA.n

*Operate/Reverse time

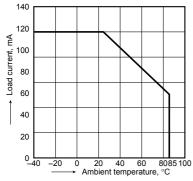


REFERENCE DATA

1. Load current vs. ambient temperature characteristics

Allowable ambient temperature: -40°C to +85°C -40°F to +185°F

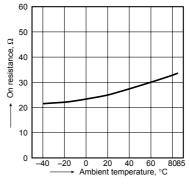




2. On resistance vs. ambient temperature characteristics

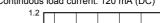
Measured portion: between terminals 4 and 6; LED current: 0 mA;

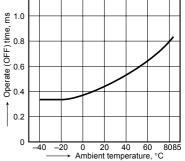
Continuous load current: 120 mA (DC)



3. Operate (OFF) time vs. ambient temperature characteristics

LED current: 5mA; Load voltage: 400 V (DC); Continuous load current: 120 mA (DC)

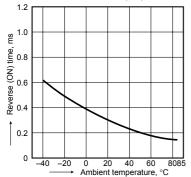




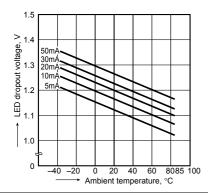
GU PhotoMOS (AQV414)

4. Reverse (ON) time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: 400 V (DC); Continuous load current: 120 mA (DC)

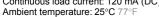


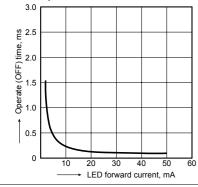
7. LED dropout voltage vs. ambient temperature characteristics LED current: 5 to 50 mA



10. Operate (OFF) time vs. LED forward current characteristics

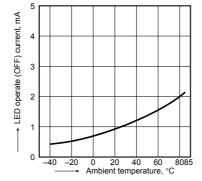
Measured portion: between terminals 4 and 6; Load voltage: 400 V (DC); Continuous load current: 120 mA (DC);





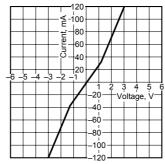
5. LED operate (OFF) current vs. ambient temperature characteristics Load voltage: 400 V (DC);

Continuous load current: 120 mA (DC)



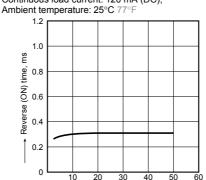
8. Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 4 and 6; Ambient temperature: 25°C 77°F



11. Reverse (ON) time vs. LED forward current characteristics

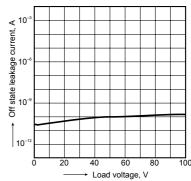
Measured portion: between terminals 4 and 6; Load voltage: 400 V (DC); Continuous load current: 120 mA (DC);



LED forward current, mA

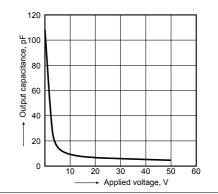
ristics of output 9. Off state leakage current vs. load voltage characteristics Measured portion: between terminals 4 and 6:

Measured portion: between terminals 4 and 6; LED current: 5 mA; Ambient temperature: 25°C 77°F



12. Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 4 and 6; Frequency: 1 MHz; Ambient temperature: 25°C 77°F



6. LED reverse (ON) current vs. ambient temperature characteristics Load voltage: 400 V (DC);

